

# Iodine Vacancy Redistribution in Organic–Inorganic Switching Effects

Advanced Materials

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Citation Report

#	ARTICLE	IF	CITATIONS
1	Wafer-scale reliable switching memory based on 2-dimensional layered organic–inorganic halide perovskite. <i>Nanoscale</i> , 2017, 9, 15278-15285.	2.8	113
2	Metal/Ion Interactions Induced p–n Junction in Methylammonium Lead Triiodide Perovskite Single Crystals. <i>Journal of the American Chemical Society</i> , 2017, 139, 17285-17288.	6.6	32
3	Competition between Metallic and Vacancy Defect Conductive Filaments in a $\text{CH}_3\text{NH}_3\text{PbI}_3$ -Based Memory Device. <i>Journal of Physical Chemistry C</i> , 2018, 122, 6431-6436.	1.5	115
4	Analytical Modeling of Organic–Inorganic $\text{CH}_3\text{NH}_3\text{PbI}_3$ Perovskite Resistive Switching and its Application for Neuromorphic Recognition. <i>Advanced Theory and Simulations</i> , 2018, 1, 1700035.	1.3	35
5	Coexistence of unipolar and bipolar resistive switching behaviors in $\text{NiFe}_2\text{O}_4$ thin film devices by doping Ag nanoparticles. <i>Journal of Applied Physics</i> , 2018, 123, .	1.1	28
6	Emerging perovskite materials for high density data storage and artificial synapses. <i>Journal of Materials Chemistry C</i> , 2018, 6, 1600-1617.	2.7	110
7	Optogenetics-Inspired Tunable Synaptic Functions in Memristors. <i>ACS Nano</i> , 2018, 12, 1242-1249.	7.3	205
8	Screening of point defects in methylammonium lead halides: a Monte Carlo study. <i>Journal of Materials Chemistry C</i> , 2018, 6, 1487-1494.	2.7	6
9	Light-current-induced acceleration of degradation of methylammonium lead iodide perovskite solar cells. <i>Journal of Power Sources</i> , 2018, 384, 303-311.	4.0	9
10	Lead-free, air-stable hybrid organic–inorganic perovskite resistive switching memory with ultrafast switching and multilevel data storage. <i>Nanoscale</i> , 2018, 10, 8578-8584.	2.8	136
11	Compliance-Free Multileveled Resistive Switching in a Transparent 2D Perovskite for Neuromorphic Computing. <i>ACS Applied Materials &amp; Interfaces</i> , 2018, 10, 12768-12772.	4.0	64
12	From dead leaves to sustainable organic resistive switching memory. <i>Journal of Colloid and Interface Science</i> , 2018, 513, 774-778.	5.0	72
13	Effects of mobile charged defects on current–voltage behavior in resistive switching memories based on organic–inorganic hybrid perovskite. <i>Applied Physics Letters</i> , 2018, 113, .	1.5	13
14	Multifunctional Optoelectronic Device Based on Resistive Switching Effects. , 0, , .		4
15	Intrinsic Behavior of $\text{CH}_3\text{NH}_3\text{PbBr}_3$ Single Crystals under Light Illumination. <i>Advanced Materials Interfaces</i> , 2018, 5, 1801206.	1.9	18
16	Control of Charge Recombination in Perovskites by Oxidation State of Halide Vacancy. <i>Journal of the American Chemical Society</i> , 2018, 140, 15753-15763.	6.6	129
17	Giant Zero-Drift Electronic Behaviors in Methylammonium Lead Halide Perovskite Diodes by Doping Iodine Ions. <i>Materials</i> , 2018, 11, 1606.	1.3	11
18	Synergies of Electrochemical Metallization and Valance Change in All–Inorganic Perovskite Quantum Dots for Resistive Switching. <i>Advanced Materials</i> , 2018, 30, e1800327.	11.1	246

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19	Biological Spiking Synapse Constructed from Solution Processed Bimetal Core-Shell Nanoparticle Based Composites. <i>Small</i> , 2018, 14, e1800288.	5.2	68
20	Phototunable Biomemory Based on Light-Mediated Charge Trap. <i>Advanced Science</i> , 2018, 5, 1800714.	5.6	99
21	Atomic Scale Photodetection Enabled by a Memristive Junction. <i>ACS Nano</i> , 2018, 12, 6706-6713.	7.3	37
22	Plasmon-Assisted Zone-Selective Repair of Nanoscale Electrical Breakdown Paths in Metal/Oxide/Metal Structures for Near-Field Optical Sensing. <i>ACS Applied Nano Materials</i> , 2018, 1, 4340-4350.	2.4	4
23	Light-Induced Anomalous Resistive Switches Based on Individual Organic-Inorganic Halide Perovskite Micro-Nanofibers. <i>Advanced Electronic Materials</i> , 2018, 4, 1800206.	2.6	26
24	1D Hexagonal $\text{HC}(\text{NH}_2)_2\text{PbI}_3$ for Multilevel Resistive Switching Nonvolatile Memory. <i>Advanced Electronic Materials</i> , 2018, 4, 1800190.	2.6	70
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26	Solution-processed resistive switching memory devices based on hybrid organic-inorganic materials and composites. <i>Physical Chemistry Chemical Physics</i> , 2018, 20, 23837-23846.	1.3	68
27	Phosphorene/ZnO Nano-Heterojunctions for Broadband Photonic Nonvolatile Memory Applications. <i>Advanced Materials</i> , 2018, 30, e1801232.	11.1	98
28	Independent Memcapacitive Switching Triggered by Bromide Ion Migration for Quaternary Information Storage. <i>Advanced Materials</i> , 2019, 31, e1806424.	11.1	38
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35	Environmentally Robust Memristor Enabled by Lead-Free Double Perovskite for High-Performance Information Storage. <i>Small</i> , 2019, 15, e1905731.	5.2	123
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38	Enhanced stability of guanidinium-based organic-inorganic hybrid lead triiodides in resistance switching. <i>APL Materials</i> , 2019, 7, .	2.2	12
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46	Unconventional CN vacancies suppress iron-leaching in Prussian blue analogue pre-catalyst for boosted oxygen evolution catalysis. <i>Nature Communications</i> , 2019, 10, 2799.	5.8	202
47	Memristors with organic-inorganic halide perovskites. <i>Informa-Materially</i> , 2019, 1, 183-210.	8.5	111
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67	Substrate-Dependent Photoconductivity Dynamics in a High-Efficiency Hybrid Perovskite Alloy. Journal of Physical Chemistry C, 2019, 123, 3402-3415.	1.5	10
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106	Two-terminal optoelectronic memory device. , 2020, , 75-105.		0
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133	Advances in Halide Perovskite Memristor from Lead-Based to Lead-Free Materials. <i>ACS Applied Materials &amp; Interfaces</i> , 2021, 13, 17141-17157.	4.0	64
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140	Ionically Mediated Mechanical Deformation Associated with Memristive Switching. <i>Advanced Functional Materials</i> , 2021, 31, 2103145.	7.8	4
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144	Advances in Flexible Memristors with Hybrid Perovskites. <i>Journal of Physical Chemistry Letters</i> , 2021, 12, 8798-8825.	2.1	36
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